1.1 Scope.

This specification covers the detail requirements for a monolithic CMOS 14-bit digital-to-analog converter for direct interfacing to both 8- and 16-bit microprocessor systems. A novel low-leakage configuration enables the AD7535 to exhibit excellent output leakage current characteristics over the specified temperature range.

1.2 Part Number.

The complete part numbers per Table 1 of this specification are as follows:

Device	Part Number[1]
−1	AD7535S(X)/883B
−2	AD7535T(X)/883B

NOTE
[1]See paragraph 1.2.3 for package identifier.

1.2.3 Case Outline.

See Appendix 1 of General Specification ADI-M-1000: package outline:

(X)	Package	Description
E	E-28	28-Contact LCC
Q	Q-28	28-Pin Cerdip

1.3 Absolute Maximum Ratings. (T_A = +25°C unless otherwise noted)

V_{DD} (Pin 26) to DGND	−0.3V, +17V
V_{SS} (Pin 27) to AGND	−15V, +0.3V
V_{REFS} (Pin 1) to AGND	±25V
V_{REFF} (Pin 2) to AGND	±25V
V_{RFB} (Pin 3) to AGND	±25V
Digital Input Voltage (Pins 8-25) to DGND	−0.3V, V_{DD}
V_{PIN4} to DGND	−0.3V, V_{DD}
AGND to DGND	−0.3V, V_{DD}
Power Dissipation	
Up to +75°C	1000mW
Derates above +75°C	10mW/°C
Operating Temperature Range	−55°C to +125°C
Storage Temperature	−65°C to +150°C
Lead Temperature (Soldering 10sec)	+300°C

1.5 Thermal Characteristics.

Thermal Resistance θ_{JC} = 35°C/W for Q-28 and E-28
θ_{JA} = 120°C/W for Q-28 and E-28

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Table 1.

Test	Symbol	Device	Design Limit T_{min}, T_{max}	Sub Group 1	Sub Group 2, 3	Sub Group 4	Test Condition[1]	Units
Resolution	RES	−1, 2	14					Bits
Relative Accuracy	RA	−1	±2	±2	±2			LSB max
		−2	±1	±2	±1	±1		
Differential Nonlinearity	DNL	−1, 2	±1	±1	±1		Guaranteed Monotonic to 14-Bits	LSB max
Gain Error[2]	A_E	−1	±8	±8	±8			LSB max
		−2	±4	±8	±4	±4		
Gain Tempco	TC_{AE}	−1	±5					ppm/°C max
		−2	±2.5					
Supply Rejection ($\Delta Gain/\Delta V_{DD}$)	PSRR	−1, 2	±0.02	±0.01	±0.02		ΔV_{DD} = ±5%	% per % max
Output Leakage Current (Pin 4)	I_{OUT}	−1, 2	±20	±5	±20		V_{SS} = −300mV (All Digital Inputs 0V)	nA max
			±150	±5	±150		V_{SS} = 0V (All Digital Inputs 0V)	
Output Current Settling Time @ 25°C	t_{SL}	−1, 2	1.5				To 0.003% of FSR. I_{OUT} LOAD = 100Ω, C_{EXT} = 13pF. DAC Register Alternately Loaded with All 1's and All 0's.	µs max
Feedthrough Error[3]	FT	−1, 2	10				V_{REF} = ±10V, 10kHz Sine Wave DAC Register Loaded with All 0's	mV p-p max
Reference Input Resistance (Pin 1)	R_{IN}	−1, 2	3.5	3.5	3.5		Typical Input Resistance = 6kΩ	kΩ min
			10	10	10			kΩ max
Digital Input High Voltage	V_{IH}	−1, 2	2.4	2.4	2.4			V min
Digital Input Low Voltage	V_{IH}	−1, 2	0.8	0.8	0.8			V max
Input Leakage Current	I_{IN}	−1, 2	±10	±1	±10		V_{IN} = 0V or V_{DD}	µA max
Input Capacitance	C_{IN}	−1, 2	7					pF max
Analog Output Capacitance Pin 3	C_{OUT}	−1, 2	260				DAC Register Loaded with All 1's	pF max
			130				DAC Register Loaded with All 0's	
$\overline{CSMSB}$ or $\overline{CSLSB}$ to $\overline{WR}$ Setup Time	t_{CWS}	−1, 2	0					ns min
$\overline{CSMSB}$ or $\overline{CSLSB}$ to $\overline{WR}$ Hold Time	t_{CWH}	−1, 2	0					ns min
$\overline{LDAC}$ Pulse Width	t_{LDAC}	−1, 2	240					ns min
Write Pulse Width	t_{WR}	−1, 2	240					ns min
Data Setup Time	t_{DS}	−1, 2	180					ns min
Data Hold Time	t_{DH}	−1, 2	30					ns min
Power Supply Voltage Range	V_{DD}	−1, 2	11.4				Specs Guaranteed Over This Range	+ V min
			15.75					+ V max
	V_{SS}	−1, 2	−200					mV min
			−300					mV max
Power Supply Current	I_{DD}	−1, 2	4	4	4		All Digital Inputs V_{IL} or V_{IH}	mA max
			500	500	500		All Digital Inputs 0 or V_{DD}	µA max

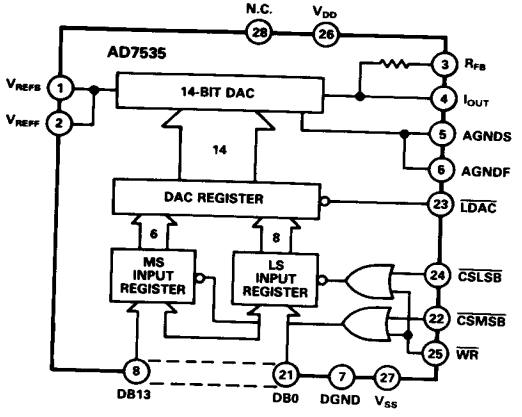
NOTES

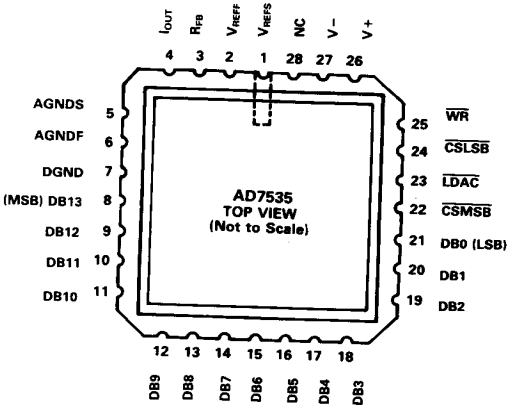
[1] V_{DD} = +12V to +15V; V_{REF} = +10V, V_{PIN3} = V_{PIN4} = 0V, V_{SS} = −300mV unless otherwise stated. Specifications are guaranteed for a V_{DD} of +12V to +15V with a tolerance of ±5%, testing is performed at 12V and 15V only.

[2] Measured using internal feedback resistor and includes effects of leakage current and gain T.C.

[3] Feedthrough can be further reduced by connecting the metal lid to ground.

3.2.1 Functional Block Diagram and Terminal Assignments.





3.2.4 Microcircuit Technology Group.

This microcircuit is covered by technology group (80).

4.2.1 Life Test/Burn-In Circuit.

Steady state life test is per MIL-STD-883, Method 1005. Burn-in is per MIL-STD-883 Method 1015, Test Condition (B).